

ABSTRACT OF THE DISCLOSURE

A semiconductor device including a substrate including an active pattern; a gate electrode crossing the active pattern; a source/drain pattern adjacent to one side of the gate electrode and on an upper portion of the active pattern; an active contact electrically connected to the source/drain pattern; and a silicide layer between the source/drain pattern and the active contact, the source/drain pattern including a body part including a plurality of semiconductor patterns; and a capping pattern on the body part, the body part has a first facet, a second facet on the first facet, and a corner edge defined where the first facet meets the second facet, the corner edge extending parallel to the substrate, the capping pattern covers the second facet of the body part and exposes the corner edge, and the silicide layer covers a top surface of the body part and a top surface of the capping pattern.

FIG. 2B